

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A method for fabricating a mask, comprising the steps of:
forming a film to be patterned,
forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern, and
increasing said surface area of said top resist pattern after said film is patterned via said laminated resist pattern.
2. (Original) The fabricating method as defined in claim 1, wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).
3. (Original) The fabricating method as defined in claim 1, wherein said top resist pattern is made of a resist material with phenol-based hydroxide.
4. (Original) The fabricating method as defined in claim 1, wherein said surface area of said top resist pattern is increased by coating a water-soluble resin at least over said top resist pattern of said laminated resist pattern.
5. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.
6. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.
7. (Original) The fabricating method as defined in claim 1, wherein said laminated resist pattern is not removed through the fabrication process of patterned thin film.

8. (Original) The fabricating method as defined in claim 1, wherein said film is patterned via said laminated resist pattern by means of dry etching.
9. (Original) A method for fabricating a patterned thin film, comprising the steps of:
 - forming a first thin film to be patterned,
 - forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern,
 - patterning said first thin film via said laminated resist pattern, to form a first patterned thin film,
 - increasing said surface area of said top resist pattern, and
 - forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern.
10. (Original) The fabricating method as defined in claim 9, wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).
11. (Original) The fabricating method as defined in claim 9, wherein said top resist pattern is made of a resist material with phenol-based hydroxide.
12. (Original) The fabricating method as defined in claim 9, wherein said surface area of said top resist pattern is increased by coating a water-soluble resin at least over said top resist pattern of said laminated resist pattern.
13. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.
14. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

15. (Original) The fabricating method as defined in claim 9, wherein said laminated resist pattern is not removed through the fabrication process of said first patterned thin film and said second patterned thin film.

16. (Original) The fabricating method as defined in claim 9, wherein said film is patterned via said laminated resist pattern by means of dry etching.

17. (Original) The fabricating method as defined in claim 9, wherein said second patterned thin film is located away from said first patterned thin film by a minute gap.

18. (Original) The fabricating method as defined in claim 17, wherein said second patterned thin film is composed of a pair of patterned thin films, which are located at both sides of said first patterned thin film by minute gaps.

19. (Currently Amended) A micro device comprising a first patterned thin film and a second patterned thin film which are formed by a fabricating method as defined in ~~any one of claims 9-18. claim 9.~~

20. (Currently Amended) A thin film magnetic head comprising a first patterned thin film and a second patterned thin film which are formed by a fabricating method as defined in ~~any one of claims 9-18. claim 9.~~

21. (Original) The thin film magnetic head as defined in claim 20, comprising a magnetoresistive effective element which is composed of said first patterned thin film.

22. (Original) The thin film magnetic head as defined in claim 20, comprising a magnetic domain controlling film which is composed of said second patterned thin film.